MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet







SMC

FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Super fast recovery time for high speed switching

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.21 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwies specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

P/N(MARK)	ES5A	ES5B	ES5C	ES5D	ES5E	ES5G	ES5J	UNITS
Maximum Recurrent Peak Reverse Voltage		100	150	200	300	400	600	V
Maximum RMS Voltage		70	105	140	210	280	600	V
Maximum DC Blocking Voltage		100	150	200	300	400	600	V
Maximum Average Forward Rectified Current								
at T∟=100°C		5.0				Α		
Peak Forward Surge Current, 8.3 ms single half sine-wave								
superimposed on rated load (JEDEC method)				120				Α
Maximum Instantaneous Forward Voltage at 5.0A		0.95 1.25 1.7			1.75	V		
Maximum DC Reverse Current Ta=25°C		5				μА		
at Rated DC Blocking Voltage Ta=100°C	500		μА					
Maximum Reverse Recovery Time (Note 1)	35		nS					
Typical Junction Capacitance (Note 2)		40			2	5	pF	
Operating and Storage Temperature Range T _J , Ts _{TG}		-65—+150				°C		

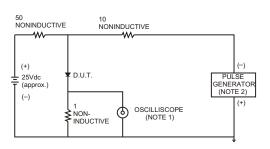
NOTES

- 1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.



RATING AND CHARACTERISTIC CURVES (ES5A THRU ES5J)

FIG.1- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERYTIME CHARACTERISTIC



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.

2. Rise Time= 10ns max., Source Impedance= 50 ohms.

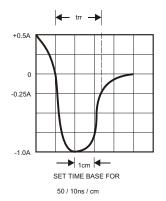


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

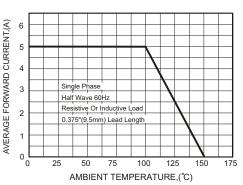
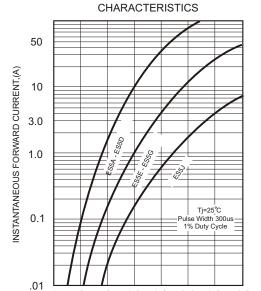


FIG.3-TYPICAL FORWARD



.8 1.0

.4 .6

FIG.4-TYPICAL REVERSE

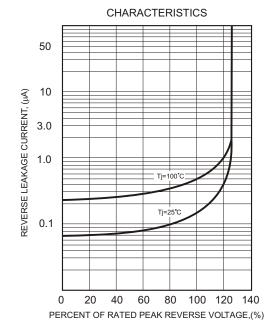


FIG.5-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

1.6

1.8

1.2 1.4

FORWARD VOLTAGE,(V)

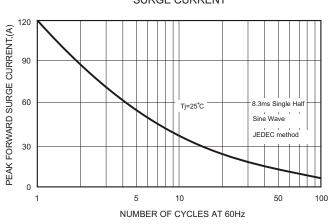
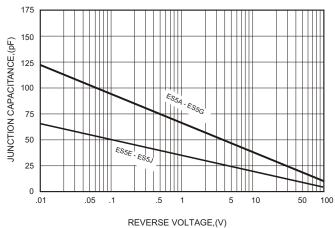


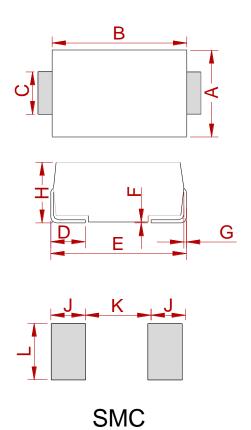
FIG.6-TYPICAL JUNCTION CAPACITANCE







PACKAGE MECHANICAL DATA



	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Max.	Min.	Max.		
Α	5.75	6.25	0.226	0.246		
В	6.90	7.40	0.272	0.291		
С	2.75	3.25	0.108	0.128		
D	0.95	1.52	0.037	0.060		
E	7.70	8.20	0.303	0.323		
F	0.051	0.203	0.002	0.008		
G	0.15	0.31	0.006	0.012		
Н	2.15	2.62	0.085	0.103		
J	2.40		0.094			
K		4.20		0.165		
L	3.30		0.130			

REEL SPECIFICATION

P/N	PKG	QTY
ES5A THRU ES5J	SMC	3000



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